



# STF13N95K3, STFI13N95K3, STP13N95K3, STW13N95K3

N-channel 950 V, 0.68  $\Omega$  typ., 10 A Zener-protected SuperMESH3™ Power MOSFET in TO-220FP, I<sup>2</sup>PAKFP, TO-220 and TO-247

Datasheet – production data

## Features

Order codes	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>	P <sub>TOT</sub>
STF13N95K3	950 V	< 0.85 $\Omega$	10 A	40 W
STFI13N95K3				190 W
STP13N95K3				
STW13N95K3				

- Gate charge minimized
- Extremely large avalanche performance
- 100% avalanche tested
- Very low intrinsic capacitance
- Zener-protected

## Applications

- Switching applications

## Description

These SuperMESH3™ Power MOSFETs are the result of improvements applied to STMicroelectronics' SuperMESH™ technology, combined with a new optimized vertical structure. These devices boast an extremely low on-resistance, superior dynamic performance and high avalanche capability, rendering them suitable for the most demanding applications.

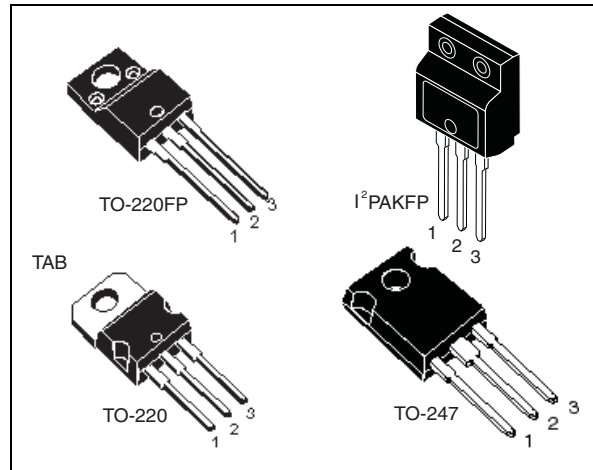


Figure 1. Internal schematic diagram

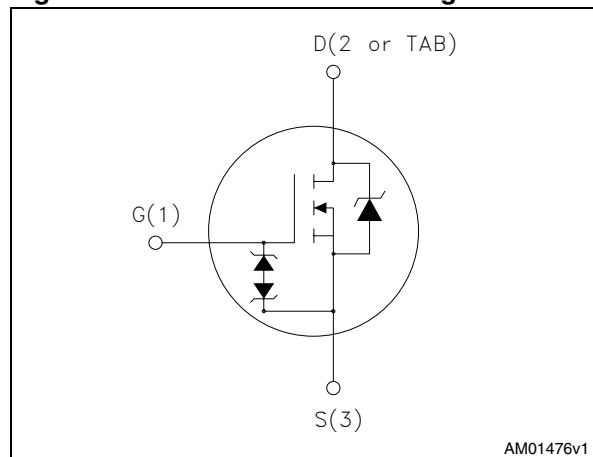


Table 1. Device summary

Order codes	Marking	Package	Packaging
STF13N95K3	13N95K3	TO-220FP	Tube
STFI13N95K3		I <sup>2</sup> PAKFP	
STP13N95K3		TO-220	
STW13N95K3		TO-247	

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220 TO-247	TO-220FP I <sup>2</sup> PAKFP	
V <sub>DS</sub>	Drain source voltage	950		V
V <sub>GS</sub>	Gate- source voltage	± 30		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	10	10 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	6	6 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	40	40 <sup>(1)</sup>	A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	190	40	W
I <sub>AR</sub>	Max current during repetitive or single pulse avalanche (pulse width limited by T <sub>jmax</sub> )	13		A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>J</sub> = 25 °C, I <sub>D</sub> =I <sub>AS</sub> , V <sub>DD</sub> = 50 V)	400		mJ
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T <sub>C</sub> = 25 °C)		2500	V
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	9		V/ns
T <sub>j</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	- 55 to 150		°C

1. Limited by maximum junction temperature.
2. Pulse width limited by safe operating area.
3. I<sub>SD</sub> ≤ 10 A, di/dt ≤ 400 A/μs, V<sub>Peak</sub> ≤ V<sub>(BR)DSS</sub>.

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		TO-220	TO-247	TO-220FP I <sup>2</sup> PAKFP	
R <sub>thj-case</sub>	Thermal resistance junction-case max	0.66		3.13	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-amb max	62.5	50	62.5	°C/W

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}, V_{GS} = 0$	950			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 950\text{V},$ $V_{DS} = 950\text{V}, T_C = 125\text{ °C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.68	0.85	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance			1620		pF
$C_{oss}$	Output capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	117	-	pF
$C_{rss}$	Reverse transfer capacitance			1.2		
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0, V_{DS} = 0\text{ to }760\text{ V}$	-	115	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related			131		
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	2.3	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 760\text{ V}, I_D = 10\text{ A}$	-	51	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 10\text{ V}$		10		
$Q_{gd}$	Gate-drain charge	(see <a href="#">Figure 20</a> )		30		

1. Time related is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 475 \text{ V}$ , $I_D = 5 \text{ A}$ , $R_G = 4.7 \text{ } \Omega$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 22</a> )		18		ns	
$t_r$	Rise time		-	16	-	ns	
$t_{d(off)}$	Turn-off delay time				50		ns
$t_f$	Fall time				21		ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		10	mA
$I_{SDM}$	Source-drain current (pulsed)				40	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 10 \text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 10 \text{ A}$ , $V_{DD} = 60 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}$ , (see <a href="#">Figure 21</a> )	-	500		ns
$Q_{rr}$	Reverse recovery charge				9	$\mu\text{C}$
$I_{RRM}$	Reverse recovery current				36	A
$t_{rr}$	Reverse recovery time	$I_{SD} = 10 \text{ A}$ , $V_{DD} = 60 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 21</a> )	-	624		ns
$Q_{rr}$	Reverse recovery charge				11	$\mu\text{C}$
$I_{RRM}$	Reverse recovery current				37	A

1. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 8. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}$	Gate-source breakdown voltage	$I_{gs} \pm 1 \text{ mA}$ , (open drain)	30	-		V

The built-in-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220FP and I<sup>2</sup>PAKFP

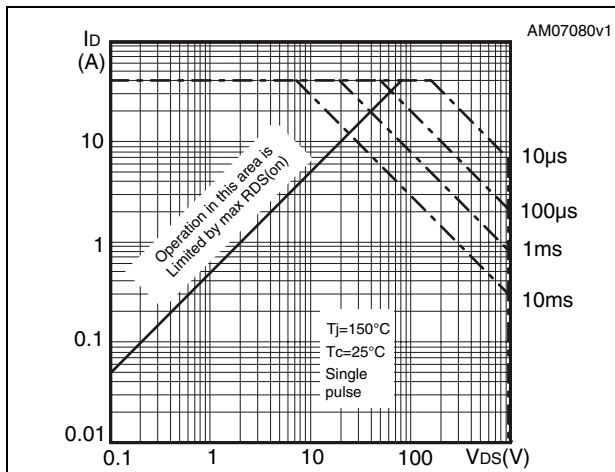


Figure 3. Thermal impedance for TO-220FP and I<sup>2</sup>PAKFP

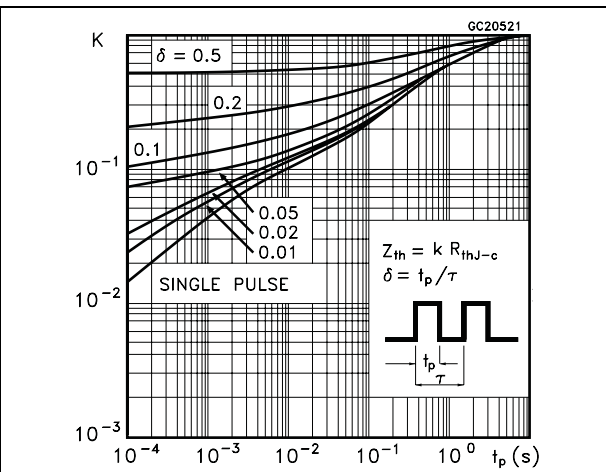


Figure 4. Safe operating area for TO-220

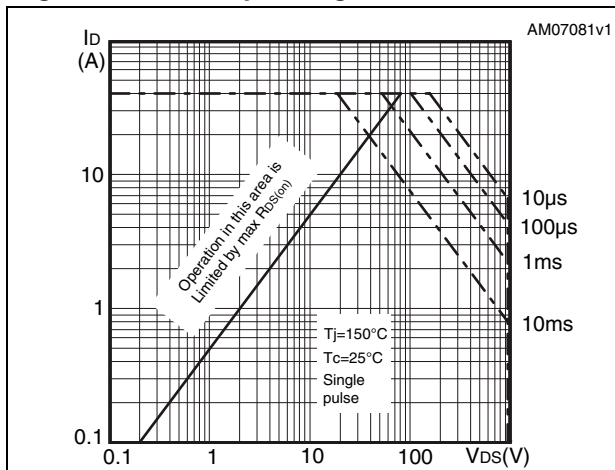


Figure 5. Thermal impedance for TO-220

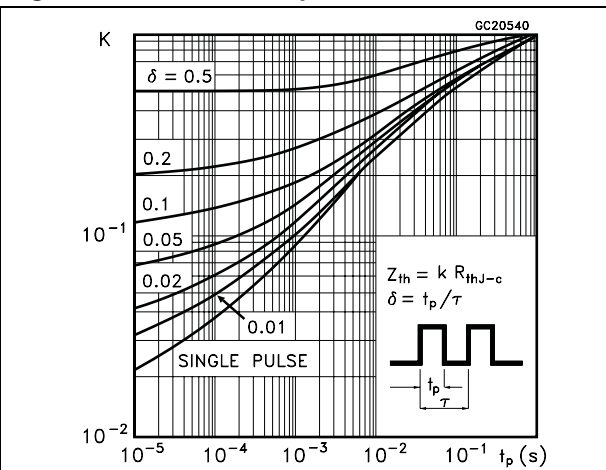


Figure 6. Safe operating area for TO-247

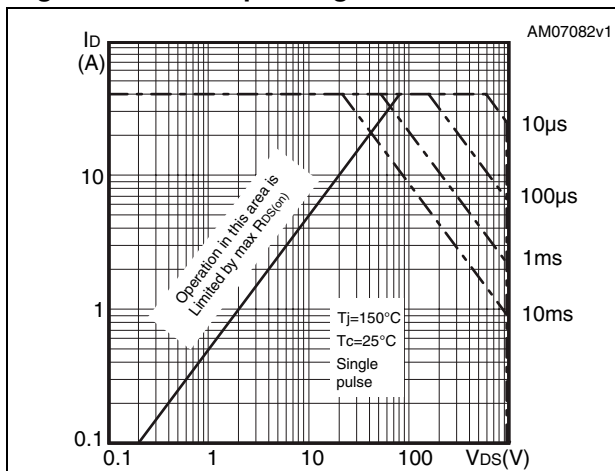


Figure 7. Thermal impedance for TO-247

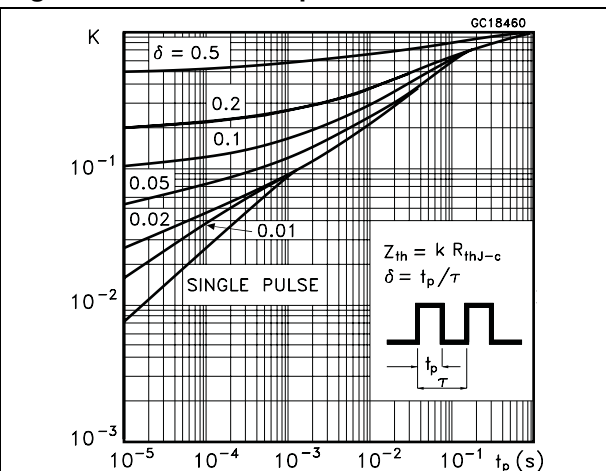


Figure 8. Output characteristics

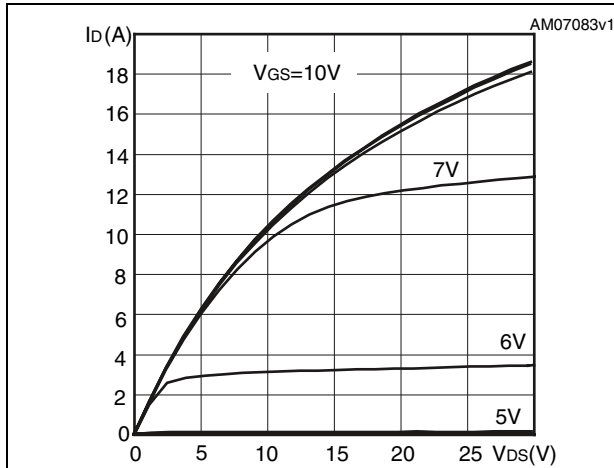


Figure 9. Transfer characteristics

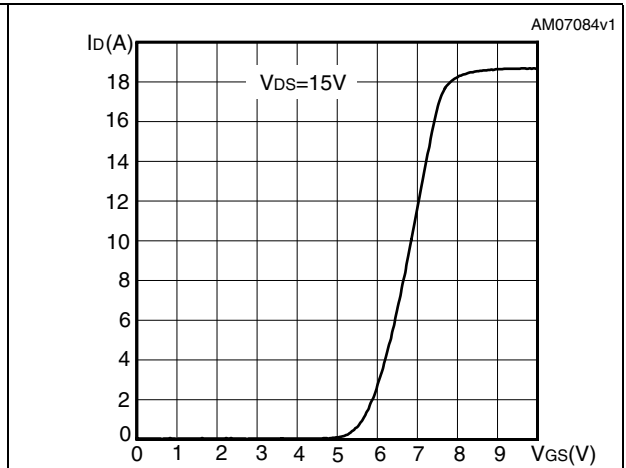


Figure 10. Gate charge vs gate-source voltage

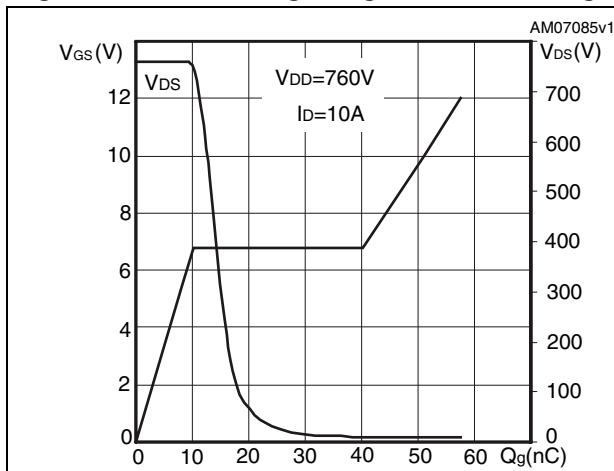


Figure 11. Static drain-source on-resistance

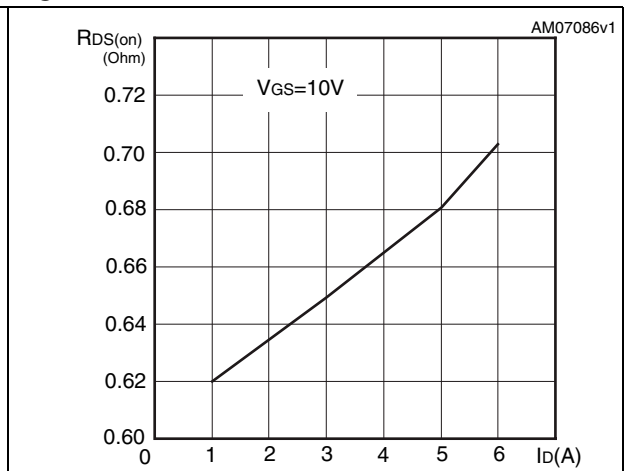


Figure 12. Capacitance variations

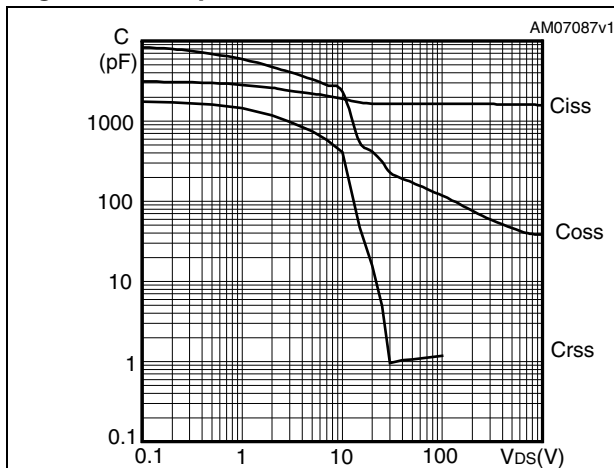


Figure 13. Output capacitance stored energy

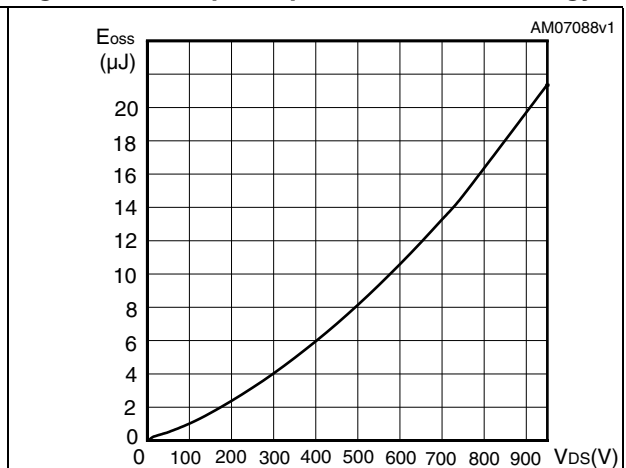


Figure 14. Normalized gate threshold voltage vs temperature

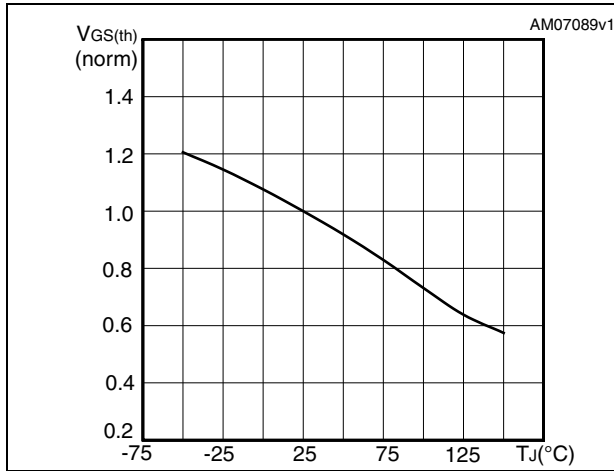


Figure 15. Normalized on-resistance vs temperature

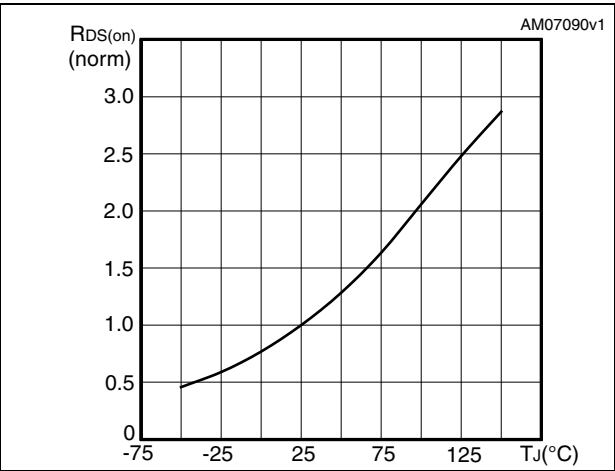


Figure 16. Source-drain diode forward characteristics

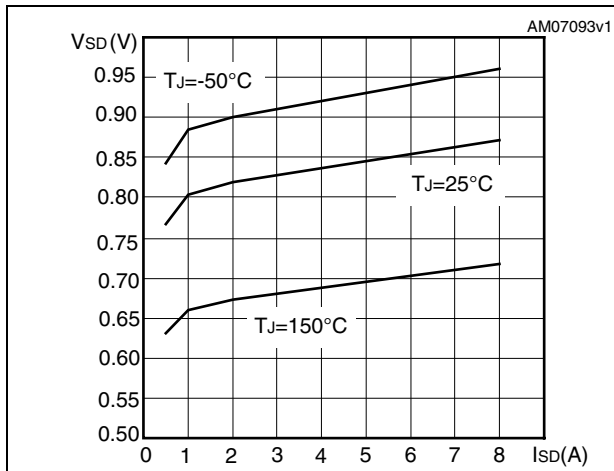


Figure 17. Normalized B<sub>VDSS</sub> vs temperature

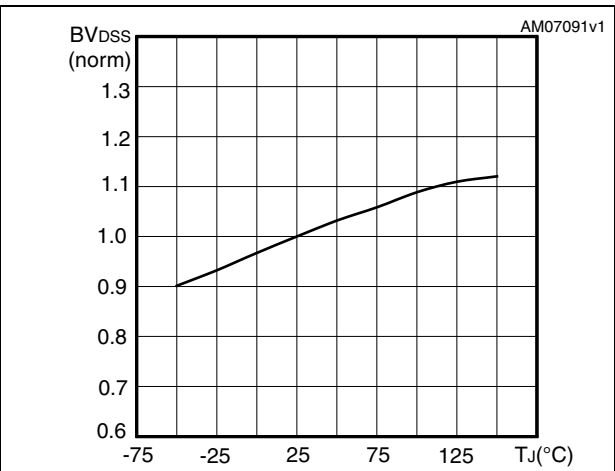
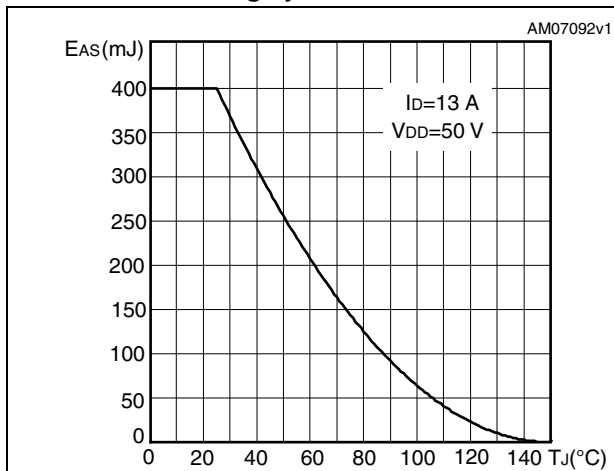


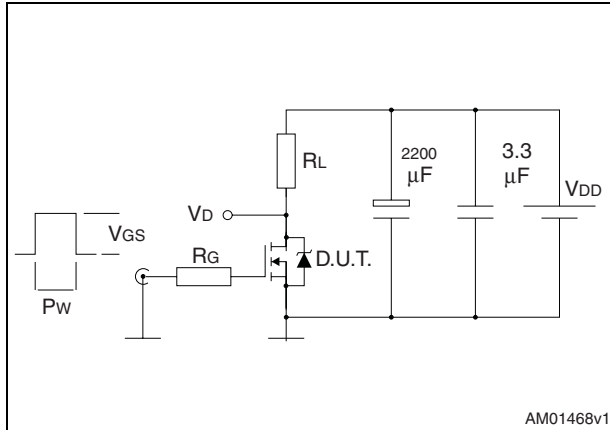
Figure 18. Maximum avalanche energy vs starting T<sub>j</sub>



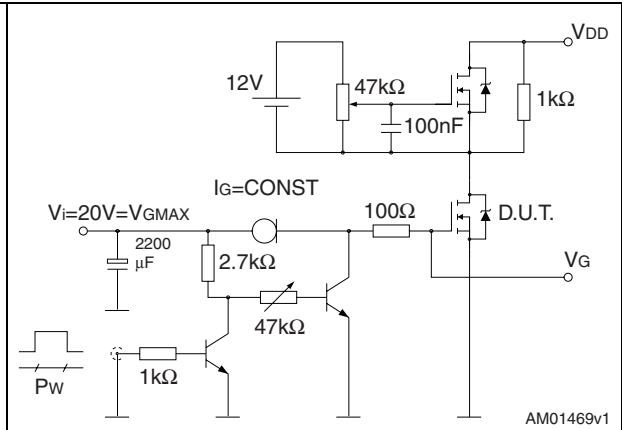


### 3 Test circuits

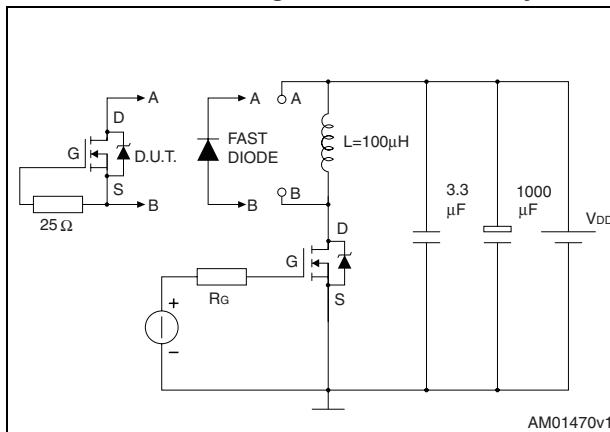
**Figure 19. Switching times test circuit for resistive load**



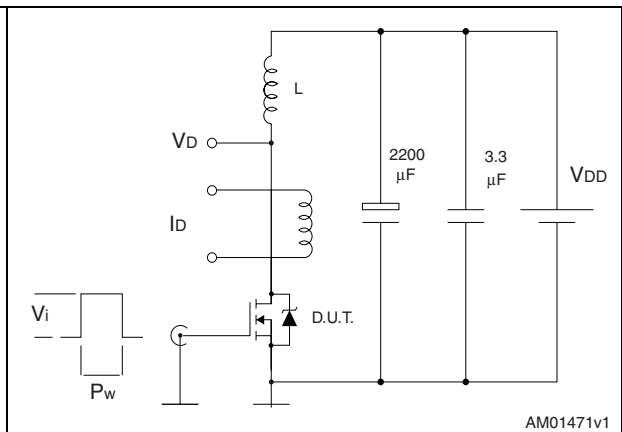
**Figure 20. Gate charge test circuit**



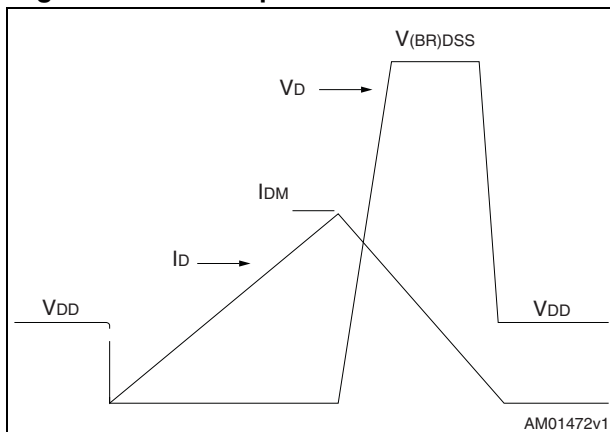
**Figure 21. Test circuit for inductive load switching and diode recovery times**



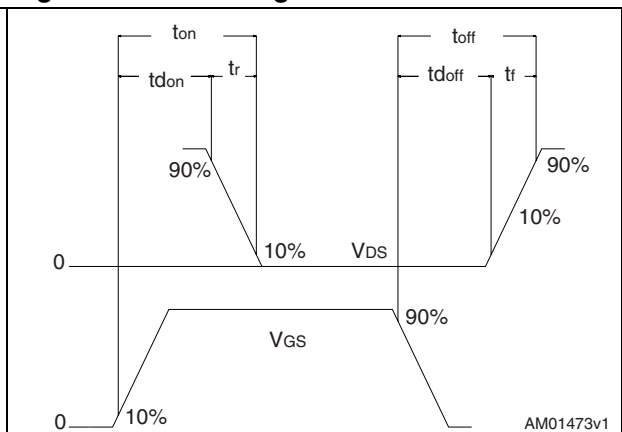
**Figure 22. Unclamped inductive load test circuit**



**Figure 23. Unclamped inductive waveform**



**Figure 24. Switching time waveform**



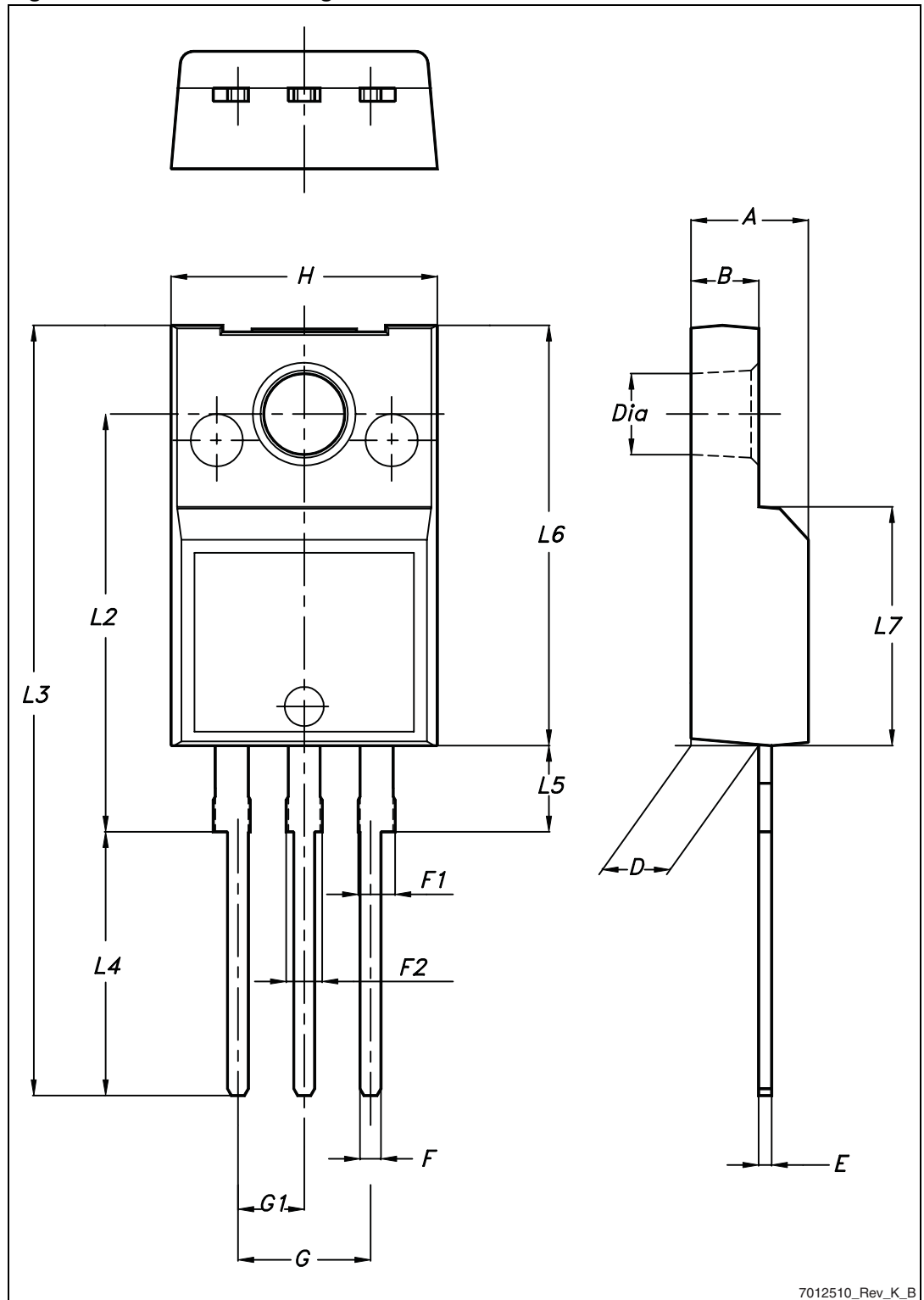
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 25. TO-220FP drawing

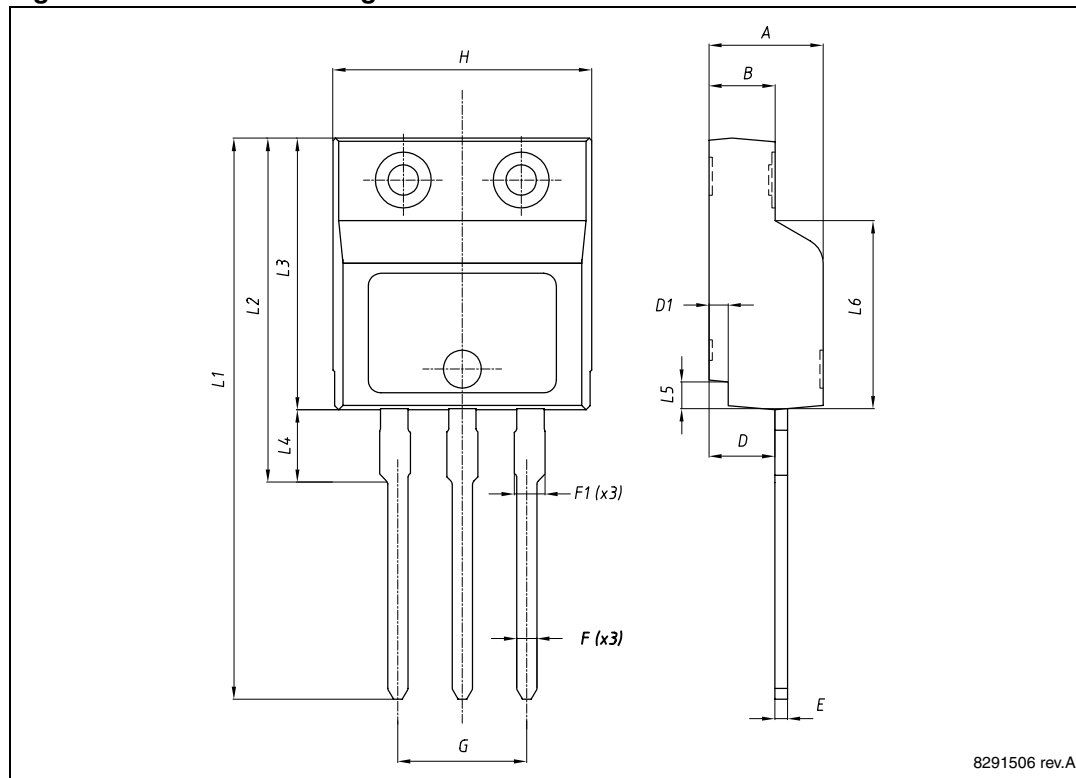


7012510\_Rev\_K\_B

Table 10. I<sup>2</sup>PAKFP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40	-	4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95		5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.30		7.50

Figure 26. I<sup>2</sup>PAKFP drawing

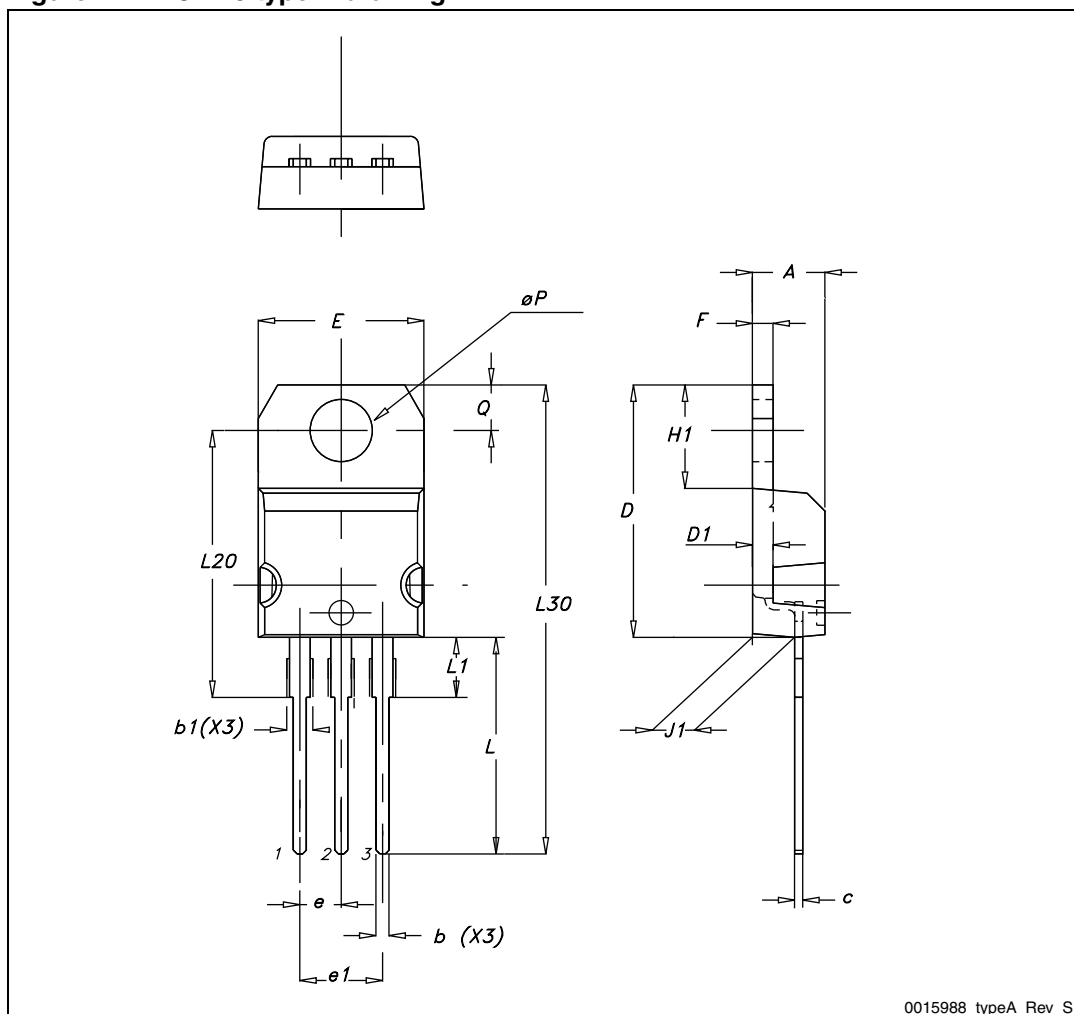


8291506 rev.A

Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 27. TO-220 type A drawing



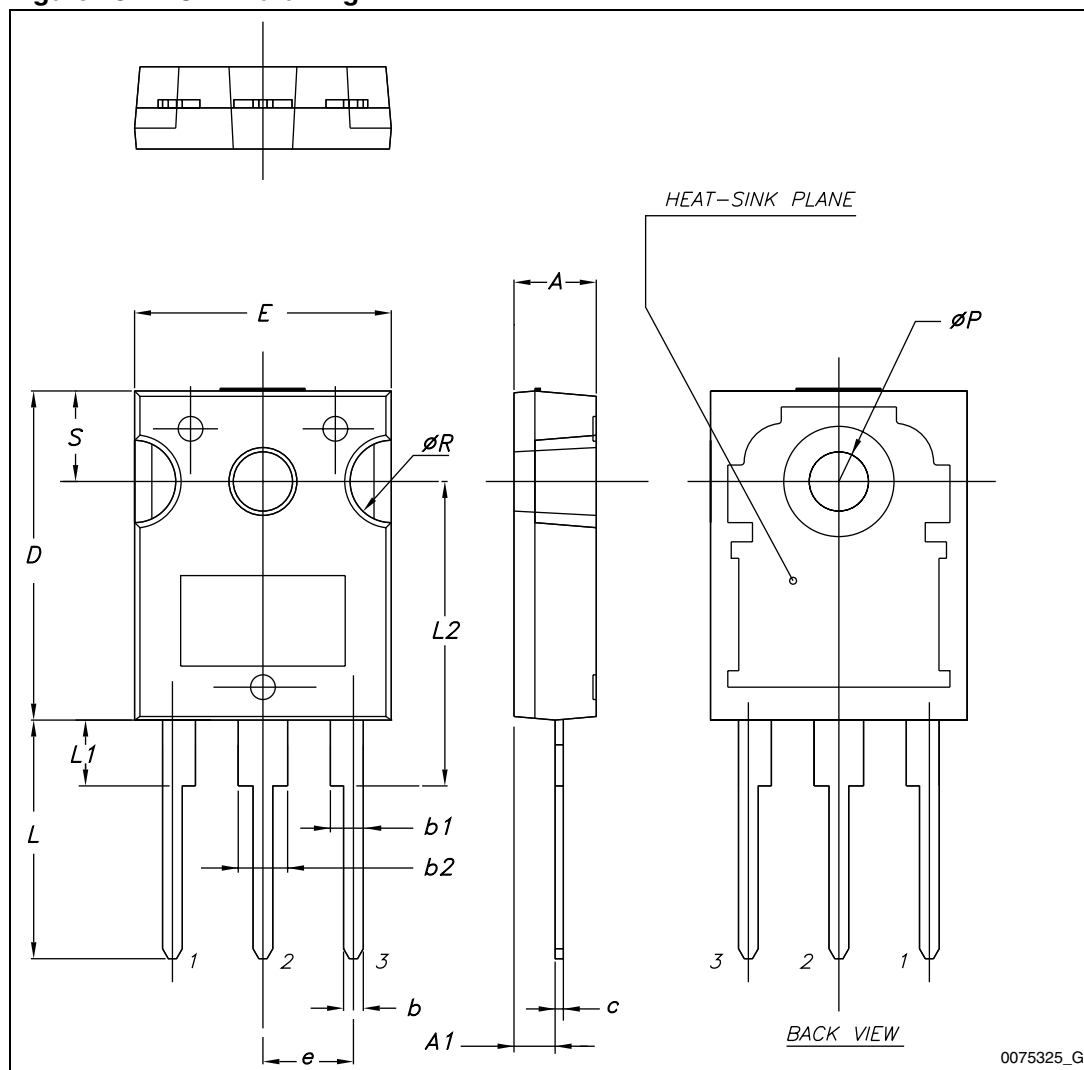
0015988\_typeA\_Rev\_S

Table 12. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70



Figure 28. TO-247 drawing



## 5 Revision history

**Table 13. Document revision history**

Date	Revision	Changes
15-May-2009	1	First release.
02-Sep-2010	2	Document status promoted from preliminary data to datasheet.
21-Jun-2012	3	Added new device in I <sup>2</sup> PAKFP. <i>Table 1: Device summary, Table 2: Absolute maximum ratings, Table 3: Thermal data, Figure 2: Safe operating area for TO-220FP and I<sup>2</sup>PAKFP, Figure 3: Thermal impedance for TO-220FP and I<sup>2</sup>PAKFP</i> have been modified accordingly. <i>Table 10: I<sup>2</sup>PAKFP mechanical data and Figure 26: I<sup>2</sup>PAKFP drawing</i> have been added.

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